

### FNK N-Channel Enhancement Mode Power MOSFET

### **Description**

The FNK3416 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  This device is suitable for use as a load switch or in PWM applications .It is ESD protested.

#### **General Features**

V<sub>DS</sub> = 20V,I<sub>D</sub> =6A

 $R_{DS(ON)}$  < 33m $\Omega$  @  $V_{GS}$ =2.5V

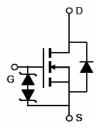
 $R_{DS(ON)}$  <27m $\Omega$  @  $V_{GS}$ =4.5V

ESD Rating: 2000V HBM

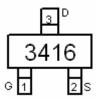
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

## **Application**

- PWM application
- Load switch



Schematic diagram



Marking and pin assignment



SOT-23 top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3416	FNK3416	SOT-23	Ø180mm	8mm	3000 units

Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	6	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	24	Α
Maximum Power Dissipation	P <sub>D</sub>	1.4	W
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}\!$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	89.3	°C/W
, and the second	1		1

### **Electrical Characteristics (T<sub>A</sub>=25 ℃ unless otherwise noted)**

Parameter	Symbol	ymbol Condition		Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20		-	٧
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μΑ



Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.45	0.7	1.0	V
Drain-Source On-State Resistance	D	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	21	27	mΩ
Diani-Source Oil-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5A	-	26	33	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =4.5A	8	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	\/ -10\/\/ -0\/	-	660	-	PF
Output Capacitance	$V_{DS}=10V,V_{GS}=0V,$ Capacitance	F=1.0MHz	-	160	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0lvii 12	-	87	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	0.5		nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =10V, $R_L$ =1.5 $\Omega$	-	1		nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =5 $V$ , $R_{GEN}$ =3 $\Omega$	-	12		nS
Turn-Off Fall Time	t <sub>f</sub>		-	4		nS
Total Gate Charge	Qg	\/ -10\/  -64	-	8		nC
Gate-Source Charge	$Q_{gs}$	$V_{DS}=10V,I_{D}=6A,$ $V_{GS}=4.5V$	-	2.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> -4.5V	-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	6	Α

### Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

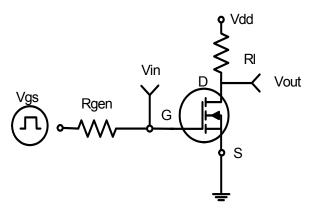
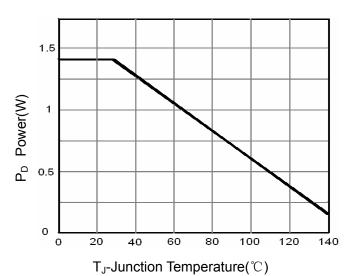
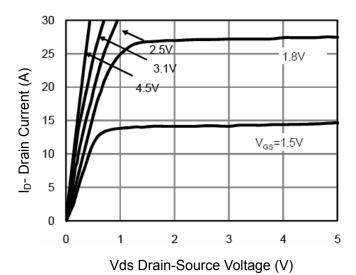


Figure 1:Switching Test Circuit



**Figure 3 Power Dissipation** 



**Figure 5 Output Characteristics** 

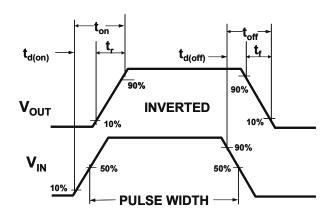
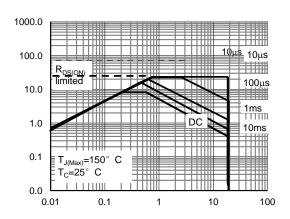


Figure 2:Switching Waveforms



Vds Drain-Source Voltage (V)

Figure 4 Safe Operation Area

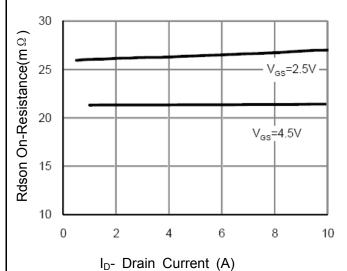
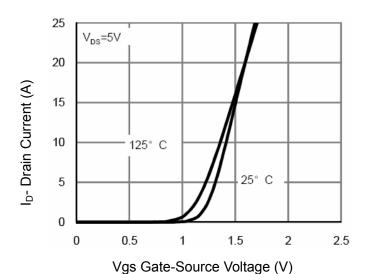


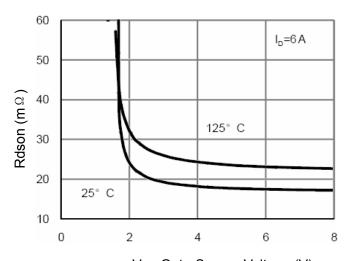
Figure 6 Drain-Source On-Resistance

Ip- Drain Current (A)





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)
Figure 9 Rdson vs Vgs

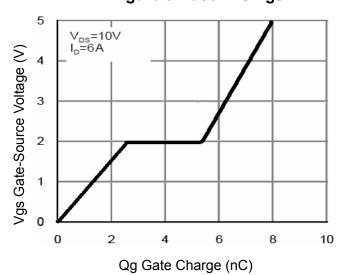


Figure 11 Gate Charge

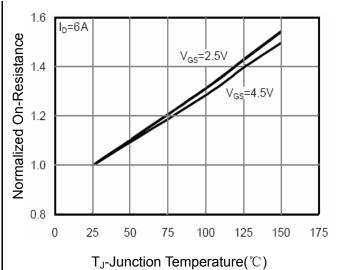


Figure 8 Drain-Source On-Resistance

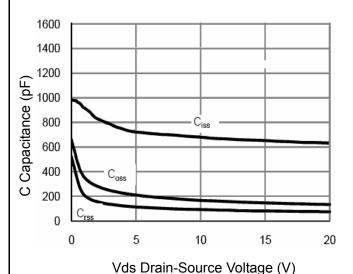


Figure 10 Capacitance vs Vds

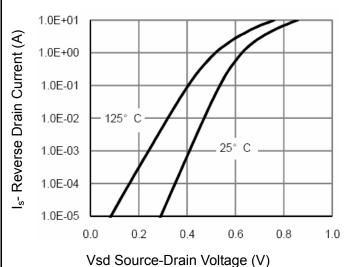


Figure 12 Source- Drain Diode Forward



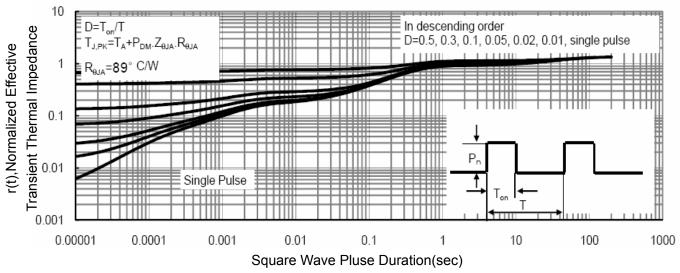
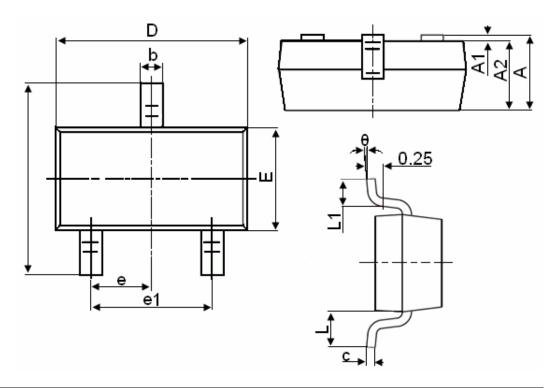


Figure 13 Normalized Maximum Transient Thermal Impedance



# **SOT-23 Package Information**



Symbol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
Е	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

#### Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



#### ATTENTION:

- FNK reserves the right to make changes to the information herein for the improvement of the design and performance without further notice! Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current.
- FNK assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all FNK products described or contained herein.
- Specifications of any and all FNK products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- FNKstrives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all FNK products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the FNK product that you intend to use.
- FNK will supply the best possible product for customers!